



**MAINTENANCE MANUAL
851-870 MHz, 100 WATT POWER AMPLIFIER
19D901841G3**

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SPECIFICATIONS*

POWER OUTPUT	100 Watts (adjustable from 50 watts to rated power output).
FCC FILING	AXATR-329
SPURIOUS AND HARMONIC EMISSION (per EIA RS-152-B Par. 4)	-13dBm output (conducted) -13dBm (Radiated)
DUTY CYCLE	Continuous
RF OUTPUT IMPEDANCE	50 ohms

*These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

WARNING

Although the highest DC voltage supplied to the transmitter is + 24VDC, high currents may be drawn under short circuit conditions. These currents can heat metal objects such as tools, rings, watchbands, etc., enough to cause burns. Be careful when working near energized 24 Volt circuits!

High level RF energy in the transmitter Power Amplifier assembly can cause RF burns upon contact. KEEP AWAY FROM THESE CIRCUITS WHEN THE TRANSMITTER IS ENERGIZED!



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Mountain View Road • Lynchburg, Virginia 24502

Printed in U.S.A.

DESCRIPTION

The 19D901841G3 800 MHz power amplifier assembly used in MASTR III station applications uses seven RF power devices to provide a maximum of 100 watts output power. R11 on the Power Control Board (19D901803G3) provides adjustment of the output power over a 3 dB range (50W to 100W).

The power amplifier assembly consists of an RF board with all the amplifier stages and an output detector, a power control board, and an isolator. A driver amp board is also located on the P.A. cover.

Supply voltage from the system board is connected to TB1 and decoupled by C6.

CIRCUIT ANALYSIS

DRIVER AMP

The driver amplifier board is located in a shielded enclosure mounted to the fan cover of the power amplifier assembly. This driver amp amplifies the +10dB (10mW) signal from the Tx synthesizer to +20 dB (100mW).

The function of the 800 MHz Buffer Amplifier is to increase the power level from the MASTR III Exciter module to a level sufficient to drive the 100 Watt MASTR II Power Amplifier.

The circuit is powered from the T/R shelf's +13 V supply. This is connected to the board at J3.6, and powers the 8V regulator, U1. The output of U1 is switched to the amplifier circuit via Q2, which is turned on by a + 5V signal applied to J3.2.

A +10 dBm RF signal is supplied at J2, and this drives the MMIC, U2, via the attenuator network R9-R11. The output of U2 drives the GaAs FET transistor, Q3. The nominal +20 dBm output of U3 appears at J1.

POWER AMPLIFIER

The driver amp output (100mW) is coupled to the amplifier input connector J1 by a 50 ohm coaxial cable. L1, C1, C2, and the base microstrip form the input matching circuit for Q1. Control voltage is applied to Q1 through a collector feed network consisting of C3, C4, and L3.

Interstage matching between Q1 and Q2 is provided by L4, L5, C6, C8, C9, and C10. Control voltage is applied to Q2 through a collector feed network consisting of Z1, C11-C13,

and L7. The output of Q2 is matched to the input of Q3 by L8, L9, C30, C15, and the base microstrip.

Supply voltage for Q3 is applied through collector feed network Z2, C16-C18, and L11. The output of Q3 is matched to 50 ohms by microstrip W2. This output is applied to a Wilkinson divider consisting of microstrips W4 and W5. R1 provides isolation between the signal paths.

Input matching for Q4 and Q5 is provided by microstrips W8 and W9. Supply voltage is applied to Q4 and Q5 by collector feed networks Z3, Z4, C20-C25, L12, and L13. Microstrips W12 and W13 provide output matching.

The outputs of Q4 and Q5 are summed by a Wilkinson combiner consisting of W16, W17, and R3. The output of the combiner is connected to pin 1 of circulator U1.

In other special applications of this power control board, U2-B, CR1, and Q5 provide a low power alarm. U1 is used to select one of four individually adjustable power levels.

In a MASTR III station application, the binary input select lines of U1 are hardwired to select power level 0 (PLO), which is adjusted by R11. R2, R5, and R8 will have no affect on the PA output power and should be set fully CCW.

R1, R4, R7, and R10 are factory adjusted values.

WARNING

The RF Power Transistors used in the transmitter contain Beryllium Oxide, a TOXIC substance. If the ceramic, or other encapsulation is opened, crushed, broken, or abraded, the dust may be hazardous if inhaled. Use care in replacing transistors of this type.

NOTE

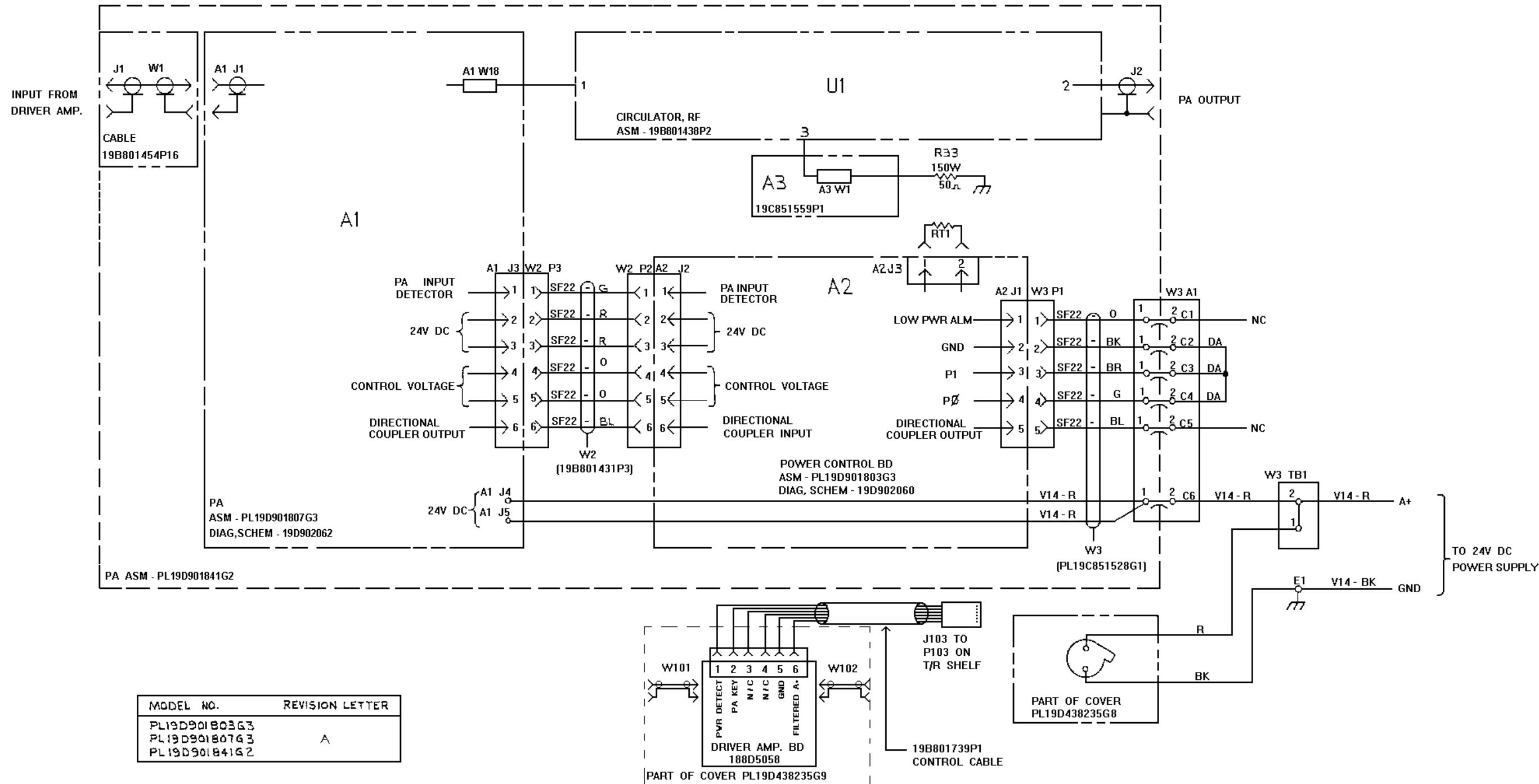
This amplifier is not field repairable. Should service become necessary, the complete power amplifier assembly must be returned to the factory for servicing.

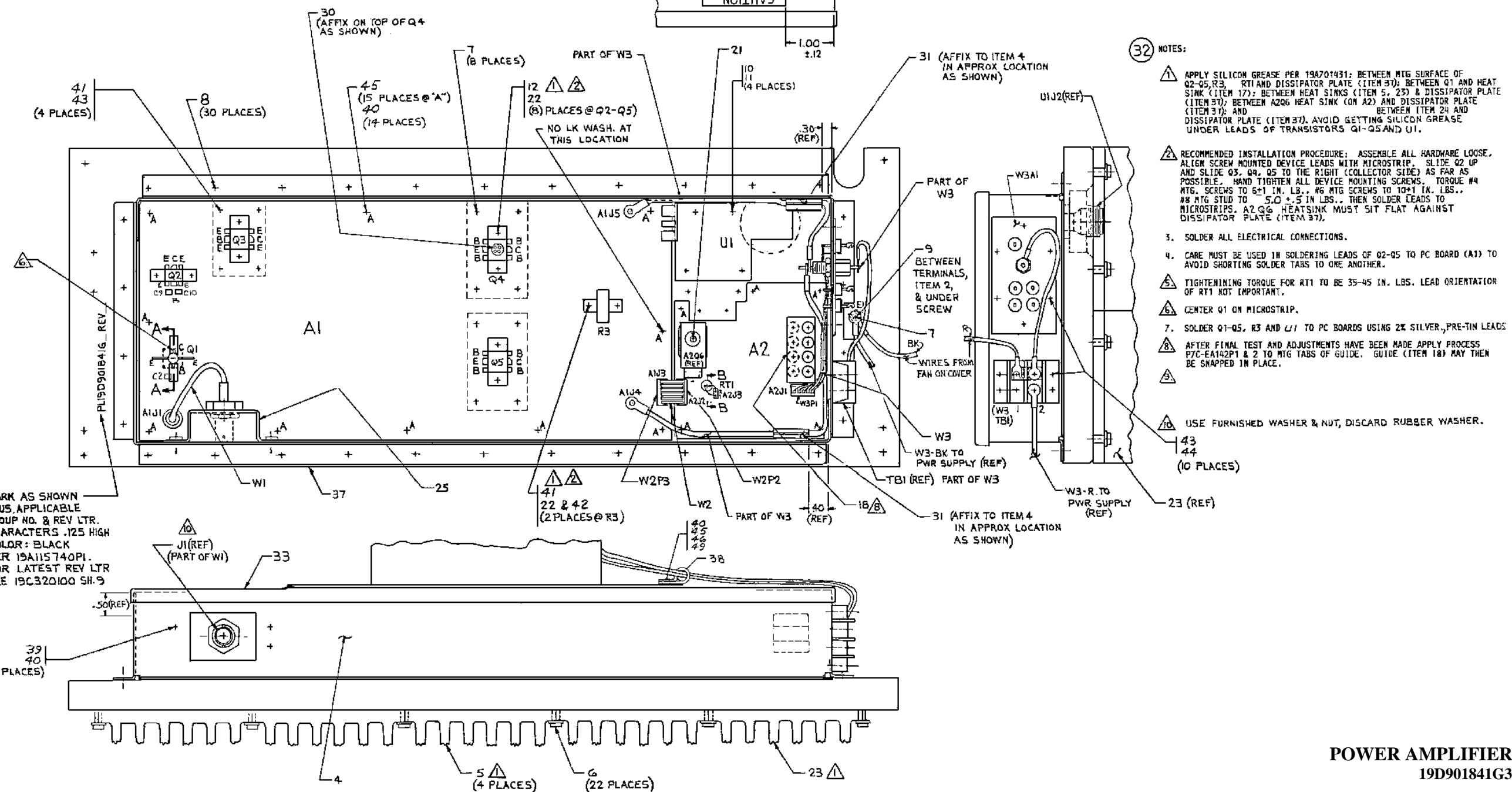
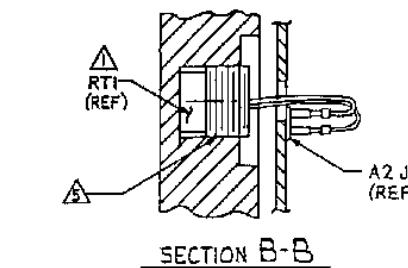
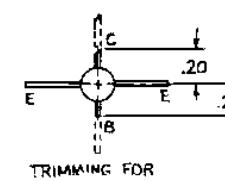
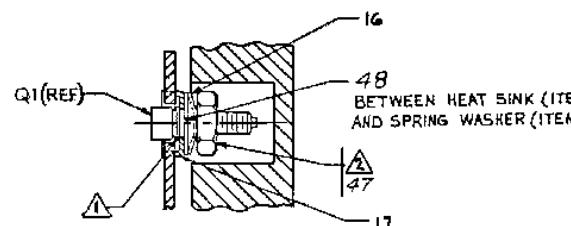
A directional coupler, W19, and detector CR1 provide a voltage, proportional to the power out, to the power control.

POWER CONTROL

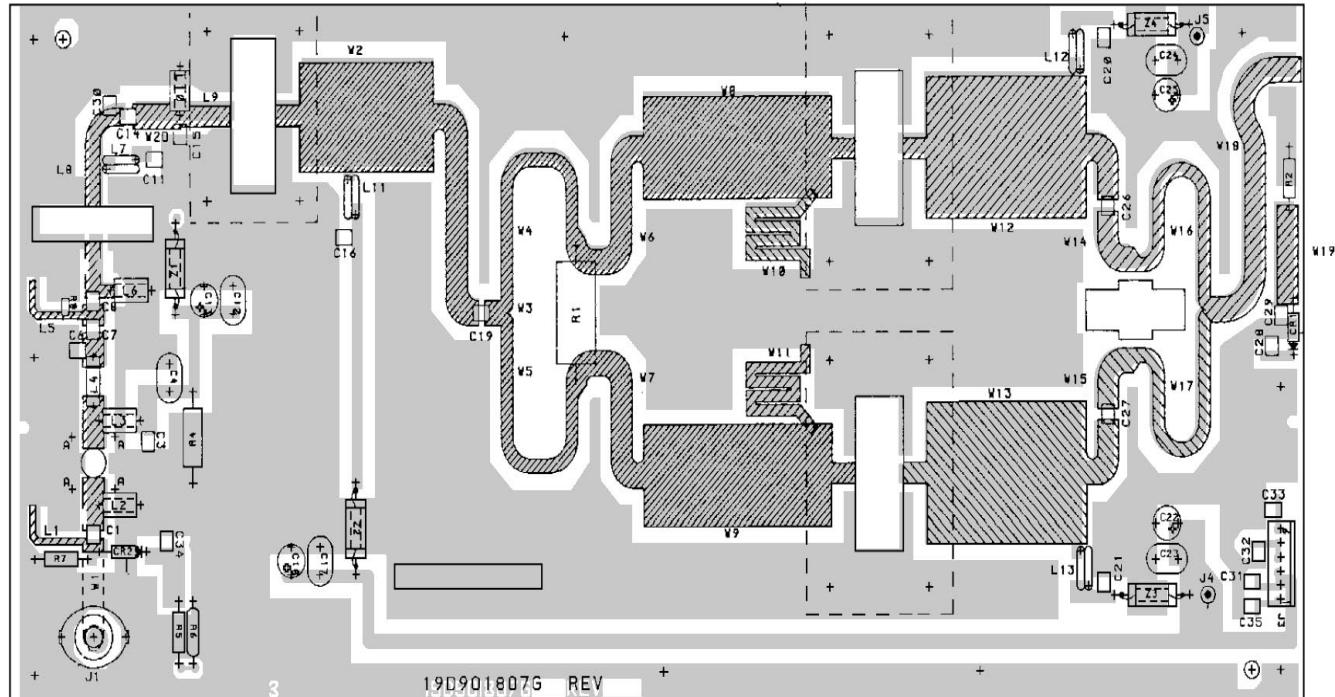
On the Power Control Board, the voltage from the detector is compared to a stable DC reference voltage in a high gain comparator, U2A. The comparator drives a DC amplifier, Q4 and pass transistor Q6 that supplies control voltage to the RF board.

Thermistor RT1 is connected to the PA heatsink and, by controlling the operation of Q2 and Q3, provides a power cut-back for ambient temperatures that exceed 70 degrees centigrade. Conduction of Q3 gradually decreases the power set voltage applied to Q4. The DC reference voltage is provided by Q1, U3, R17-19, and C5.

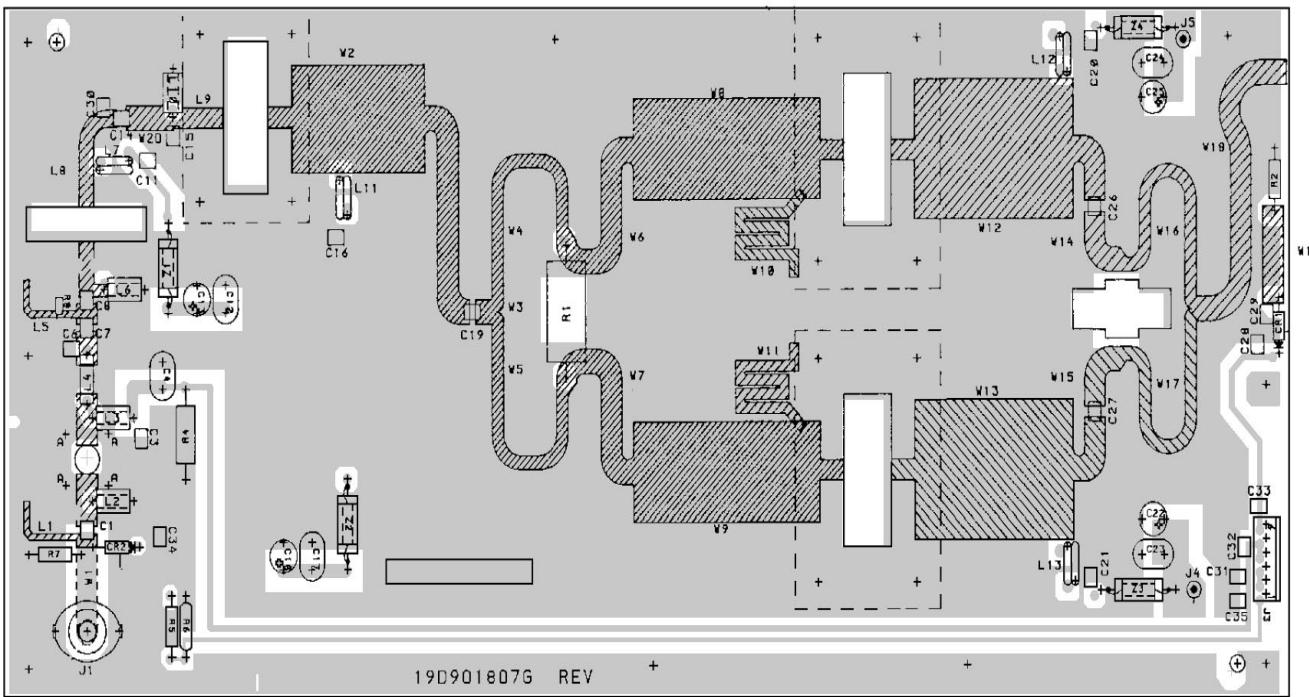




COMPONENT SIDE



SOLDER SIDE

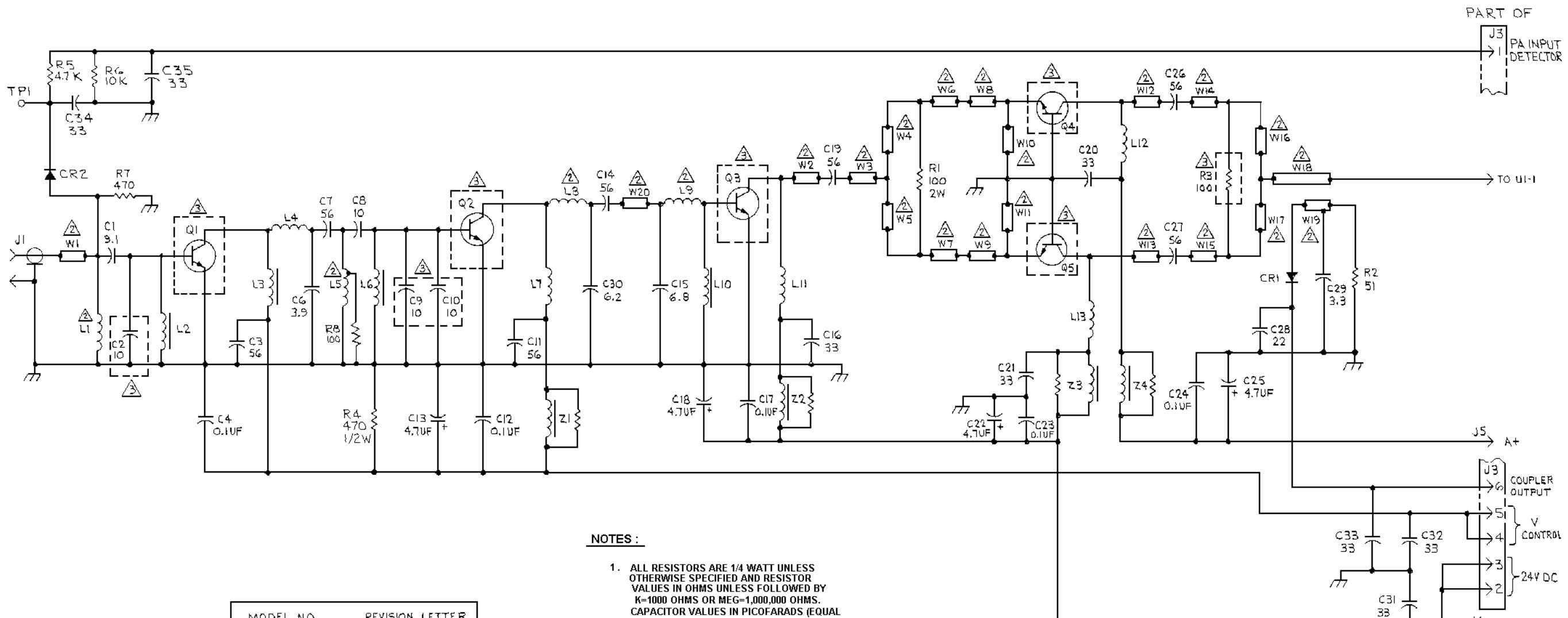


(15) NOTES:

1. SOLDER ALL ELECTRICAL CONNECTIONS.
2. COMPONENT LEADS TO PROTRUDE .060 MAX.
BELOW SOLDER SIDE OF BOARD.
- ▲** INDICATES FRONT OF COMPONENT AUTO-INSERTION
MACHINES.
4. THE FOLLOWING ITEMS ARE MOS DEVICES
REQUIRING SPECIAL CARE PER 19A701294:
U1.

POWER AMPLIFIER
19D901841G3

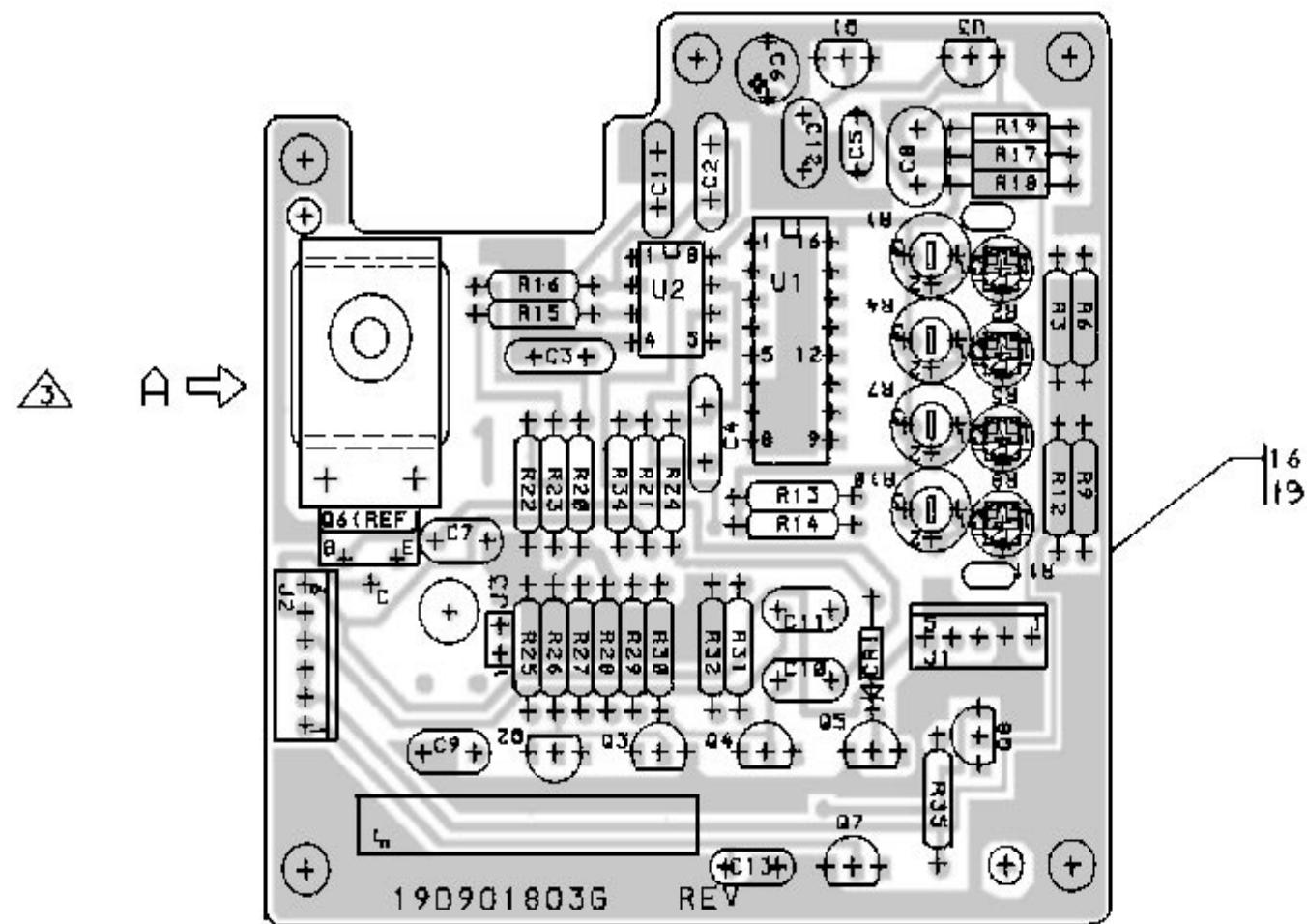
(19D901807, Sh. 2, Rev. 6)
(19D705468, Sh. 1, Rev. 3)
(19A705468, Sh. 2, Rev. 1)



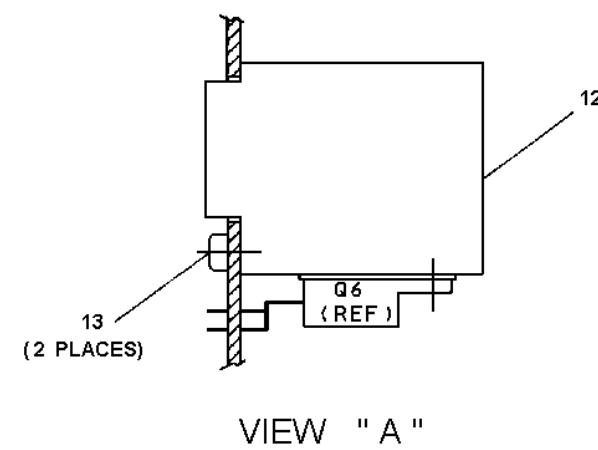
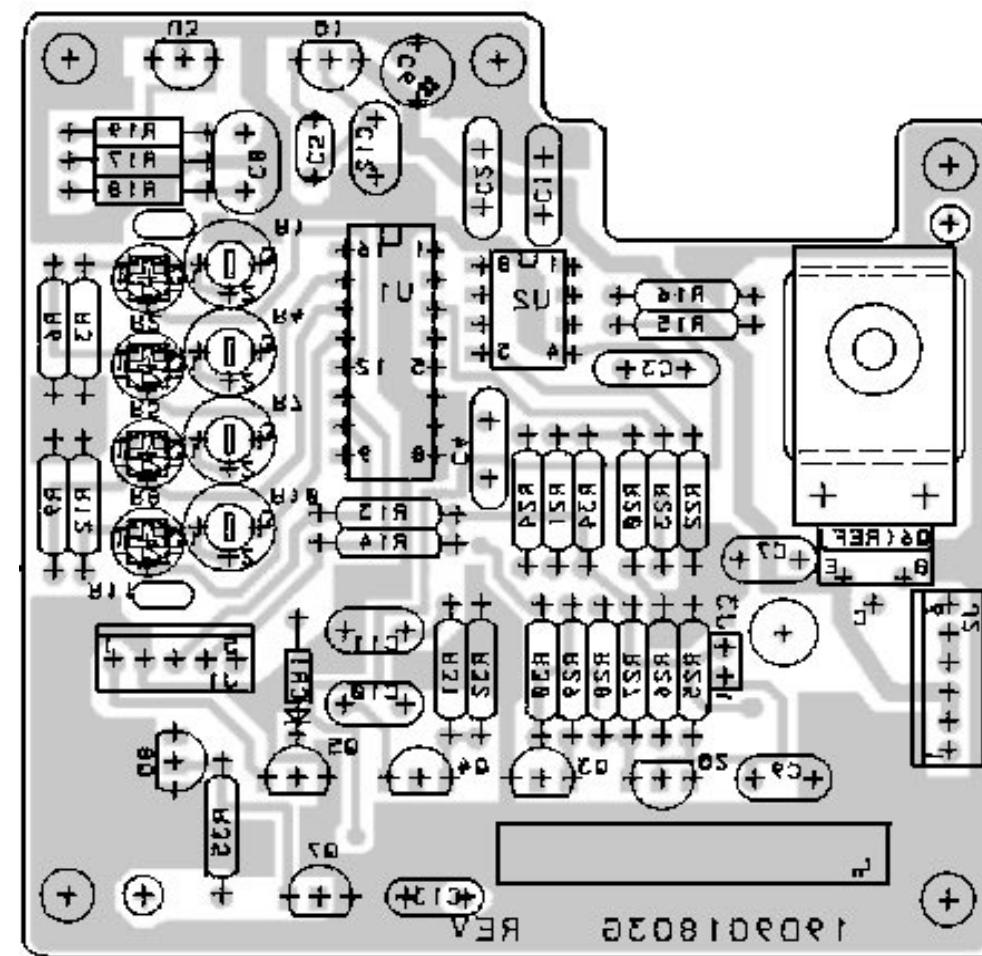
POWER AMPLIFIER
19D901841G3

(19D902062, Rev. 4)

COMPONENT SIDE



SOLDER SIDE



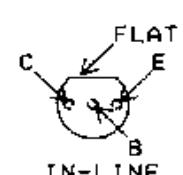
VIEW "A"

POWER AMPLIFIER
19D901803G3

(19D901803, Sh. 1, Rev. 1)
(19D902059, Component Side, Rev. 1)
(19D902059, Solder Side, Rev. 1)



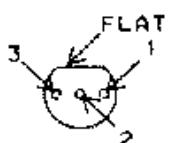
LEAD IDENTIFICATION
FOR Q1-Q5, Q7 AND Q8



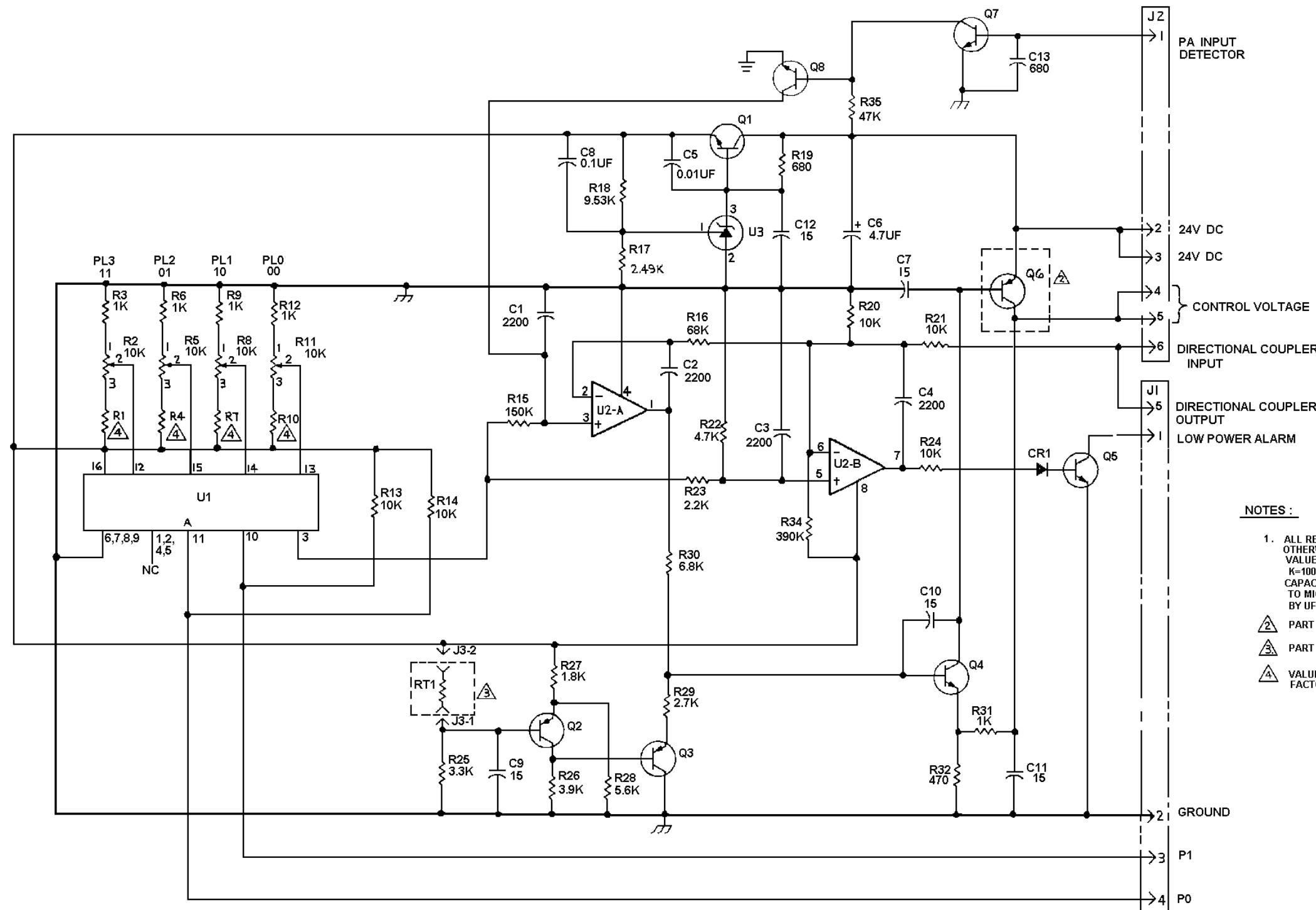
TOP VIEW

NOTE: CASE SHAPE IS DETERMINING
FACTOR FOR LEAD IDENTIFICATION.

LEAD IDENTIFICATION
FOR U3

IN-LINE
TOP VIEW

NOTE: CASE SHAPE IS DETERMINING
FACTOR FOR LEAD IDENTIFICATION.



MODEL NO.	REVISION LETTER
PL19D901803G3	A

POWER CONTROL BOARD
19D901803G3

**851-870 MHz 100 WATT POWER AMPLIFIER
19D901841G3**

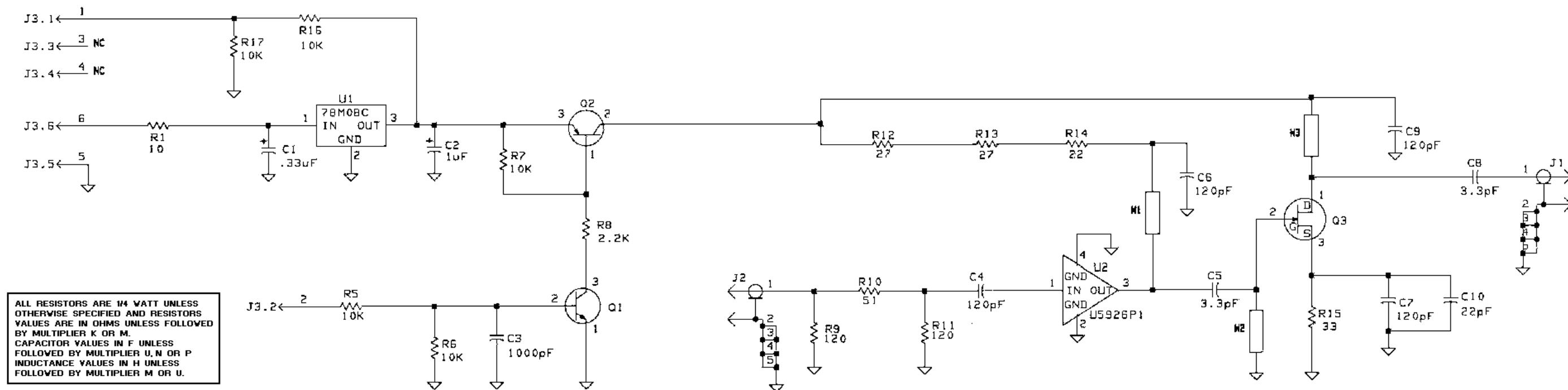
SYMBOL	PART NUMBER	DESCRIPTION
Power Amplifier Board 19D901807G3		
A1		CAPACITORS
C1	19A702232P12	Ceramic: 9.1 pF ±5%, 50 VDCW.
C3	19A702232P31	Ceramic: 56 pF ±5%, 50 VDCW.
C4	19A702250P113	Polyester: 0.1 µF ±10%, 50 VDCW.
C6	19A702232P3	Ceramic: 3.9 pF .25 pF, 50 VDCW.
C7	19A702232P31	Ceramic: 56 pF ±5%, 50 VDCW.
C8	19A705108P13	Mica Chip: 10 pF %5, 500 VDCW, temp coef 0 + 200 PPM/C.
C9 and C10	19A705108P13	Mica Chip: 10 pF %5, 500 VDCW, temp coef 0 + 200 PPM/C.
C11	19A702232P31	Ceramic: 56 pF ±5%, 50 VDCW.
C12	19A702250P113	Polyester: 0.1 µF ±10%, 50 VDCW.
C13	19A701534P6	Tantalum: 4.7 µF ±20%, 35 VDCW.
C14	19A702232P31	Ceramic: 56 pF ±5%, 50 VDCW.
C15	19A705108P9	Mica: 6.8 pF .25 pF, 500 VDCW.
C16	19A705108P25	Mica Chip: 33 pF ±5%, 500 VDCW, temp coef 0 + 50 PPM/C.
C17	19A702250P113	Polyester: 0.1 µF ±10%, 50 VDCW.
C18	19A701534P6	Tantalum: 4.7 µF ±20%, 35 VDCW.
C19	19A702232P31	Ceramic: 56 pF ±5%, 50 VDCW.
C20 and C21	19A705108P25	Mica Chip: 33 pF ±5%, 500 VDCW, temp coef 0 + 50 PPM/C.
C22	19A701534P6	Tantalum: 4.7 µF ±20%, 35 VDCW.
C23 and C24	19A702250P113	Polyester: 0.1 µF ±10%, 50 VDCW.
C25	19A701534P6	Tantalum: 4.7 µF ±20%, 35 VDCW.
C26 and C27	19A702232P31	Ceramic: 56 pF ±5%, 50 VDCW.
C28	19A702232P21	Ceramic: 22 pF ±5%, 50 VDCW.
C29	19A702232P1	Ceramic: 3.3 pF .25 pF, 50 VDCW.
C30	19A705108P8	Mica: 6.2 pF .25 pF, 500 VDCW.
C31 thru C35	19A705108P25	Mica Chip: 33 pF ±5%, 500 VDCW, temp coef 0 + 50 PPM/C.
DIODES		
CR1 and CR2	19A700047P3	Silicon: 100 mW; sim to 1N6263.
JACKS		
J1	19A700049P2	Connector, receptacle; 500 VDCW maximum; sim to NTTF-1058.
J2		PART OF U1
J3	19A704852P32	Printed wire, two part: 6 contacts, sim to Molex 22-29-2061.
J4 and J5	19A134263P1	Contact, electrical: sim to Selectro 229-1082-00-0-590.
INDUCTORS		
L1		PART OF PWB
L2	19A701091G1	Coil.
L3	19A701091G1	Coil.
L4	19A701006P7	Strap.

SYMBOL	PART NUMBER	DESCRIPTION
PART OF PWB		
L5	19A701091G1	PART OF PWB
L6	19A701091G1	Coil.
L7	19A136533P2	Coil.
PART OF PWB		
L8 and L9		
L10	19A701091G1	Coil.
L11 thru L13	19A136533P2	Coil.
TRANSISTORS		
Q1	19A703479P1	N Channel, field effect. sim to RF 2060.
Q2	19A703480P4	Silicon, NPN: Sim to MRF-891.
Q3	19A705125P1	Silicon, NPN: Sim to MRF-895.
Q4 and Q5	19A705125P2	Silicon, NPN: Sim to MRF-898.
RESISTORS		
R1	19A700111P39	Composition: 100 ohms ±5%, 2w.
R2	19A700106P32	Composition: 51 ohms ±5%, 1/4w.
R3	19A143832P1	Power: 100 ohms ±5%, 75w.
R4	19A700113P55	Composition: 470 ohms ±5%, 1/2 w.
R5	H212CRP247C	Deposited carbon: 4.7K ohms ±5%, 1/4 w.
R6	H212CRP310C	Deposited carbon: 10K ohms ±5%, 1/4 w.
R7	19A700106P55	Composition: 470 ohms ±5%, 1/4 w.
R8	19B800607P101	Metal film: 100 ohms ±5%, 1/8 w.
INTEGRATED CIRCUITS		
U1	19B802097P2	Circulator: 120 Watts.
CABLES		
W1 thru W20		PART OF PWB
FILTER		
Z1	19A701091G2	Filter.
Z2 thru Z4	19A701092G1	Filter.
	19B801426P2	Plate Support.
	19B801426P1	Plate Support.
Power Control Board 19D901803G3		
CAPACITORS		
C1 thru C4	19A700233P9	Ceramic: 2200 pF ±20%, 50 VDCW.
C5	T644ACP310K	Polyester: .010 µF ±10%, 50 VDCW.
C6	19A701534P6	Tantalum: 4.7 µF ±20%, 35 VDCW.
C7	19A701624P12	Ceramic, disc: 15 pF ±5%, 500 VDCW, temp coef 0 PPM 30.
C8	19A702250P113	Polyester: 0.1 µF ±10%, 50 VDCW.
C9 thru C12	19A701624P12	Ceramic, disc: 15 pF ±5%, 500 VDCW, temp coef 0 PPM 30.
C13	19A700233P6	Ceramic: 680 pF ±20%, 50 VDCW.
DIODES		
CR1	19A700028P1	Silicon: 75 mA, 75 PIV; sim to 1N4148.
JACKS		
J1	19A704852P31	Connector: 5 contacts; sim to Molex 22-29-2051.

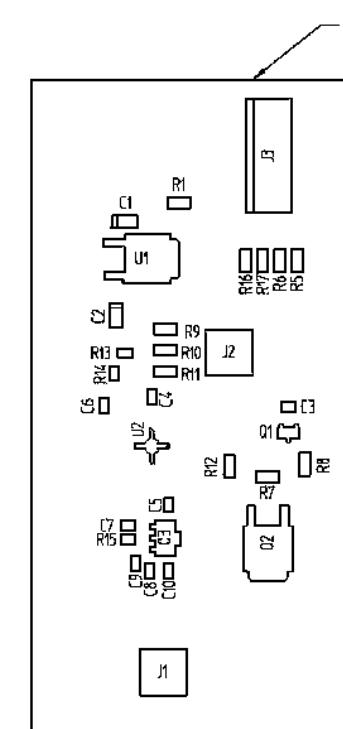
SYMBOL	PART NUMBER	DESCRIPTION
Printed wire, two part: 6 contacts, sim to Molex 22-29-2061.		
J2	19A704852P32	Printed wire, two part: 6 contacts, sim to Molex 22-29-2061.
J3	19A700072P1	Printed wire: 2 contacts rated @ 2.5 amps; sim to Molex 22-03-2021.
TRANSISTORS		
Q1	19A700023P2	Silicon, NPN: sim to 2N3904.
Q2 and Q3	19A700022P2	Silicon, PNP: sim to 2N3906.
Q4 and Q5	19A700023P2	Silicon, NPN: sim to 2N3904.
Q6	19A700055P1	Silicon, PNP. (Included with Heat Sink Assembly 19B801427G4).
RESISTORS		
R1	19A134248P4	Variable, cermet, 4 turns: 25K ohms ±10%, 1/2 w; sim to Bourns 3339P-1-253.2 w; sim to Bourns 3339P-1-253.
R2	19B800779P10	Variable: 10K ohms 2±5%, 100 VDCW, .3 watt
R3	H212CRP210C	Deposited carbon: 1K ohms ±5%, 1/4 w.
R4	19A134248P4	Variable, cermet, 4 turns: 25K ohms ±10%, 1/2 w; sim to Bourns 3339P-1-253.2 w; sim to Bourns 3339P-1-253.
R5	19B800779P10	Variable: 10K ohms 2±5%, 100 VDCW, .3 watt
R6	H212CRP210C	Deposited carbon: 1K ohms ±5%, 1/4 w.
R7	19A134248P4	Variable, cermet, 4 turns: 25K ohms ±10%, 1/2 w; sim to Bourns 3339P-1-253.2 w; sim to Bourns 3339P-1-253.
R8	19B800779P10	Variable: 10K ohms 2±5%, 100 VDCW, .3 watt
R9	H212CRP210C	Deposited carbon: 1K ohms ±5%, 1/4 w.
R10	19A134248P4	Variable, cermet, 4 turns: 25K ohms ±10%, 1/2 w; sim to Bourns 3339P-1-253.2 w; sim to Bourns 3339P-1-253.
R11	19B800779P10	Variable: 10K ohms 2±5%, 100 VDCW, .3 watt
R12	H212CRP210C	Deposited carbon: 1K ohms ±5%, 1/4 w.
R13 and R14	H212CRP310C	Deposited carbon: 10K ohms ±5%, 1/4 w.
R15	H212CRP415C	Deposited carbon: 0.15M ohms ±5%, 1/4 w.
R16	H212CRP368C	Deposited carbon: 68K ohms ±5%, 1/4 w.
R17	19A701250P239	Metal film: 2490 ohms ±1%, 250 VDCW, 1/4 watt.
R18	19A701250P295	Metal film: 9.53K ohms ±1%, 1/4 w.
R19	H212CRP168C	Deposited carbon: 680 ohms ±5%, 1/4 w.
R20 and R21	H212CRP310C	Deposited carbon: 10K ohms ±5%, 1/4 w.
R22	H212CRP247C	Deposited carbon: 4.7K ohms ±5%, 1/4 w.
R23	H212CRP222C	Deposited carbon: 2.2K ohms ±5%, 1/4 w.
R24	H212CRP310C	Deposited carbon: 10K ohms ±5%, 1/4 w.
R25	H212CRP233C	Deposited carbon: 3.3K ohms ±5%, 1/4 w.
R26	H212CRP239C	Deposited carbon: 3.9K ohms ±5%, 1/4 w.
R27	H212CRP218C	Deposited carbon: 1.8K ohms ±5%, 1/4 w.
R28	H212CRP256C	Deposited carbon: 5.6K ohms ±5%, 1/4 w.
R29	H212CRP227C	Deposited carbon: 2.7K ohms ±5%, 1/4 w.
R30	H212CRP268C	Deposited carbon: 6.8K ohms ±5%, 1/4 w.
R31	H212CRP210C	Deposited carbon: 1K ohms ±5%, 1/4 w.
R32	H212CRP147C	Deposited carbon: 470 ohms ±5%, 1/4 w.
R33	19A143832P	Power: 50 ohms ±5%, 150 watts (Used with A3).

SYMBOL	PART NUMBER	DESCRIPTION
DEPOSITED CARBON		
R34	H212CRP439C	Deposited carbon: 0.39M ±5%, 1/4 w.
R35	H212CRP347C	Deposited carbon: 47K ohms ±5%, 1/4 w.
THERMISTOR		
RT1	19A702176G2	Thermistor: 40K ohms ±20%.
INTEGRATED CIRCUITS		
U1	19A700029P36	Digital: Single 8-Channel Multiplexer; sim to 4051B.
U2	19A701789P2	Linear: Dual Op Amp; sim to LM358.

SYMBOL	PART NUMBER	DESCRIPTION	SYMBOL	PART NUMBER	DESCRIPTION
		----- RESISTORS -----			
R1	19B800607P100	Metal Film: 10 ohms, ±5%, 1/8w.	17	19A148323P1	Heat Sink.
R5 thru R7	19B800607P103	Metal Film: 10K ohms, ±5%, 1/8w.	18	19C851552P1	Power Limiter Guide.
R8	19B800607P222	Metal Film: 2.2K ohms, ±5%, 1/8w.	20	NP280071	Nameplate. (CAUTION).
R9	19B800607P121	Metal Film: 120 ohms, ±5%, 1/8w.	21	19B201074P320	Tap screw, Phillips POZIDRIV: No. 6-32 x 1-1/4.
R10	19B800607P510	Metal Film: 51 ohms, ±5%, 1/8w.	22	N405P5B6	Lock Washer.
R11	19B800607P121	Metal Film: 120 ohms, ±5%, 1/8w.	23	19B226212G5	Heat Sink
R12 and R13	19B800607P270	Metal Film: 27 ohms, ±5%, 1/8w.	25	19A705097G2	Connector Support Assembly
R14	19B800607P220	Metal Film: 22 ohms, ±5%, 1/8w.	30	19A705329P1	Temperature indicator: sim to Tempil Division of Big Three Industries Cat. No. BU-175/79. Industries Cat. No. BU-1X/78.
R15	19B800607P330 19B801251P180	Metal Film: 33 ohms, ±5%, 1/8w. OR Metal Film: 18 ohms, ±5%, 1/8w.	31	19A116552P3	Cable clip: sim to Richco KKC-4.
R16 and R17	19B800607P103	Metal Film: 10K ohms, ±5%, 1/8w.	37	19B801423G3	Plate.
		----- INTERGRATED CIRCUITS -----	38	19A701863P13	Cable clip.
U1	19A704971P10	Voltage Regulator: 8V; sim to MC78M08CDT.	39	N80P13004B6	Screw, machine: Pan head; No. 6-32 x 1/4".
U2	19A705926P1	MMIC: sim to Minicircuits MAR-45M.	40	N404P13B6	Lockwasher, internal tooth: No. 6.
		----- CABLES -----	41	N80P9005B6	Machine screw, pan head, steel, No. 4-40UNC x 5/16".
W1	19A705075P1	Cable Assembly.	42	N402P5B6	Washer: narrow, steel.
W2	19B801431P3	Cable.	43	N404P11B6	Loackwasher, internal tooth, No. 4.
W3	19C851528G1	Cable Assembly. Includes:	44	7141225P2	Nut, Hex: 4-40.
C1 thru C5 C6	5493392P7	Ceramic, feed thru: 1000 pF -0+100%, 500 VDCW.	45	N80P13006B6	Machine screw: Pan head, Phillips; No. 8-32 x 3/8"
	19A116708P1	Ceramic: 0.01 µF -0 +100%, 500 VDCW, rated 20 amps; sim to Erie 327050X5W0103P.ps; sim to Erie 327050X5W0103P.	46	N402P7B6	Flatwasher, narrow: No. 6.
2	19B801425P1	Plate.	47	N210P15B6	Nut, hex: No. 8-32.
3	7139898P3	Nut, hex, brass: No. 1/4-28.	48	N402P8B6	Flatwasher, steel: No. 8.
P1	19A700041P31	Shell.	49	7141225P3	Hex Nut: No. 6-32.
		----- MISCELLANEOUS -----	51	19D438235G9	Fan Assembly.
2	19C301087P1	Terminal board.	53	7776570P10	Connector Adapter
3	19A704779P26	Contacts: 22-30 AWG; sim to Molex 08-55-0101, Qty of 10.			
4	7143961P1	Bus bar: sim to Kulka No. 600.			
6	19B209268P113	Terminal, solderless: sim to AMP 2-34835-4.			
18	19B209268P115	Terminal: Ring Tongue, sim to AMP 34852.			
30	N80P13006B6	Machine screw: Pan head, Phillips; No. 8-32 x 3/8"			
35	344A3805P1	Contact: Crimp Type, sim to AMP 350650-1.			
36	344A3804P1	Connector Cap.			
W4	19B801454P16	Cable Assembly.			
		----- MISCELLANEOUS -----			
4	19B801424G1	Frame.			
5	19B226212G1	Heat sink.			
6	19B209103P410	Tap screw, hex head: No. 8-32 x 5/8.			
7	19B201074P308	Tap screw, Phillips POZIDRIV: No. 6-32 x 1/2.			
8	19B209103P306	Tap screw, hex head: No. 6-32 x 3/8.			
9	N403P13B6	Lockwasher: No. 6.			
10	N81P9012	Machine screw.			
11	N414P11	Lockwasher, internal tooth: No. 4.			
12	N44P9006B6	Machine screw, fillister head.			
16	5492178P2	Washer, spring tension: sim to Wallace Barnes 375-20.			



(188D5056, Rev. 3)



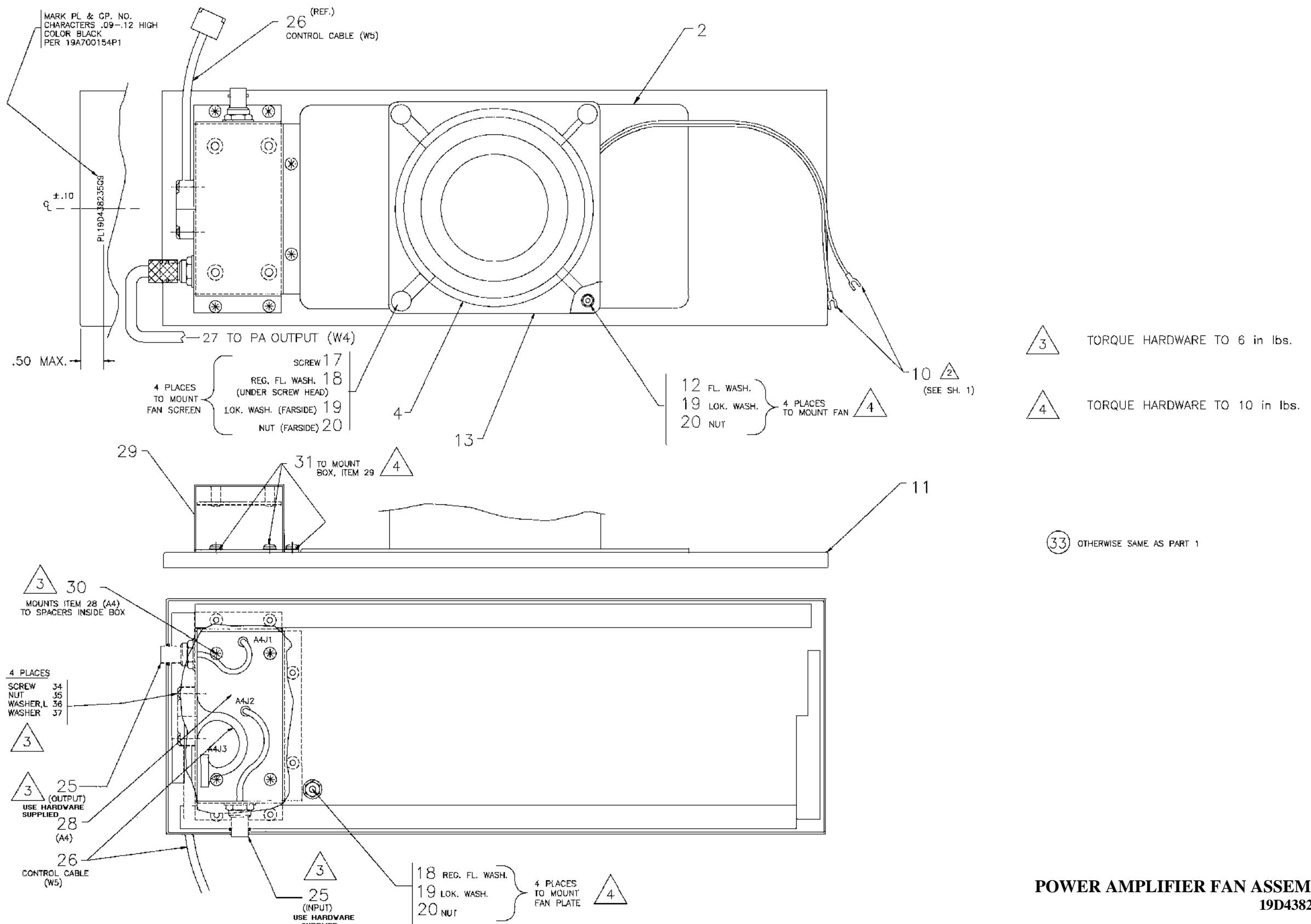
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- NOTES:
1. SOLDER ALL ELECTRICAL CONNECTIONS.
 2. COMPONENT LEADS TO PROTRUDE .060 MAX. BELOW SOLDER SIDE OF BOARD.
 3. MARK APPLICABLE GROUP AND REVISION PER 19A15740P1.09 HIGH, COLOR BLACK.
FOR LATEST REVISION NUMBER SEE REVISION LETTER INDEX.
- ▲ INDICATES FRONT OF COMPONENT AUTO-INSERTION MACHINES.

LEAD IDENTIFICATION FOR
Q1
(SOT) TRANSISTORS
(TOP VIEW)
(B) 2 □ 3 (C)
(E) 1 □

LEAD IDENTIFICATION FOR
Q3
(SOT) TRANSISTORS
(TOP VIEW)
(B) 2 □ 3 (C)
(E) 1 □

BUFFER AMPLIFIER
188D5056G1



(19D438235, Sh. 2, Rev. 1)